

Abstract

A method of producing a single crystal according to Czochralski method comprising the steps of, charging polycrystalline material into a crucible, heating and melting the polycrystalline material by a heater disposed so as to surround the crucible, immersing a seed crystal into the material melt and then pulling the seed crystal to grow a single crystal, wherein in the case of growing a single crystal of which resistivity is controlled by doping with boron, the highest temperature of the crucible is controlled to be 1600°C or less to grow the single crystal. Thereby, there is provided a method of producing a single crystal in which generation of dislocation is prevented when a single crystal having high gettering property and doped with boron is produced, and thus the single crystal can be produced at high productivity and at low cost.